

Vishay Siliconix

Bi-Directional P-Channel 20-V (D-S) MOSFET

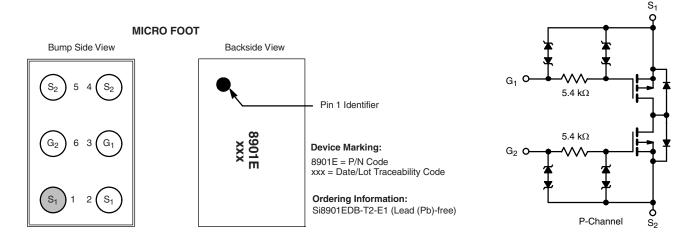
PRODUCT SUMMARY					
V _{S1S2} (V)	R_{S1S2(on)} (Ω)	I _{S1S2} (A)			
- 20	0.060 at V _{GS} = - 4.5 V	- 4.4			
	0.080 at V _{GS} = - 2.5 V	- 3.9			
	0.105 at V _{GS} = - 1.8 V	- 3.4			

FEATURES

- TrenchFET[®] Power MOSFET
- Ultra-Low R_{SS(on)}
- ESD Protected: 6000 V
- MICRO FOOT[®] Chipscale Packaging Reduces Footprint Area, Profile (0.65 mm) and On-Resistance Per Footprint Area

APPLICATIONS

• Smart Batteries for Portable Devices



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Source1- Source2 Voltage		V _{S1S2}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Source1- Source2 Current (T _J = 150 °C)	T _A = 25 °C	I _{S1S2}	- 4.4	- 3.5	А
	T _A = 85 °C		- 3.2	- 2.5	
Pulsed Source1- Source2 Current	I _{SM}	-			
	T _A = 25 °C	P-	1.7	1	W
Maximum Power Dissipation ^a	T _A = 85 °C	P _D	0.8	0.5	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Package Reflow Conditions ^c	IR/Convection		260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum humation to Ambianta	t ≤ 5 s	R _{thJA}	60	75		
Maximum Junction-to-Ambient ^a	Steady State		95	120	°C/W	
Maximum Junction-to-Foot ^b	Steady State	R _{thJF}	18	22		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. The foot is defined as the top surface of the package.

c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.



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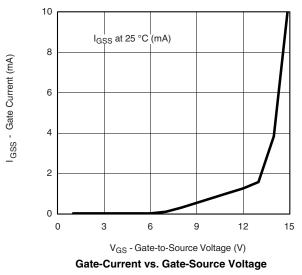
SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static	•		•	•			
Gate Threshold Voltage	V _{GS(th)}	$V_{SS} = V_{GS}, I_D = -350 \ \mu A$ - 0.45			- 1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{SS} = 0 V, V_{GS} = \pm 4.5 V$			± 4	μA	
		$V_{SS} = 0 V, V_{GS} = \pm 12 V$			± 10	mA	
Zero Gate Voltage Source Current	I _{S1S2}	$V_{SS} = -20 V, V_{GS} = 0 V$			- 1		
		V_{SS} = - 20 V, V_{GS} = 0 V, T_{J} = 85 °C			- 5 μA		
On-State Source Current ^a	I _{S(on)}	$V_{SS} = -5 V, V_{GS} = -4.5 V$	- 5			А	
		V _{GS} = - 4.5 V, I _{SS} = - 1 A		0.048	0.060	Ω	
Source1- Source2 On-State Resistance	R _{S1S2(on)}	V _{GS} = - 2.5 V, I _{SS} = - 1 A		0.062	0.080		
		V _{GS} = - 1.8 V, I _{SS} = - 1 A		0.081	0.105	1	
Forward Transconductance ^a	9 _{fs}	V _{SS} = - 10 V, I _{SS} = - 1 A		7		S	
Dynamic ^b			•	•			
Turn-On Delay Time	t _{d(on)}			2.3	3.5		
Rise Time	t _r	V_{SS} = - 10 V, R_L = 10 Ω		2.2	3.5	μs	
Turn-Off Delay Time	t _{d(off)}	$I_{SS}\cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		1.3	2		
Fall Time	t _f			9	14		
lataa.					•		

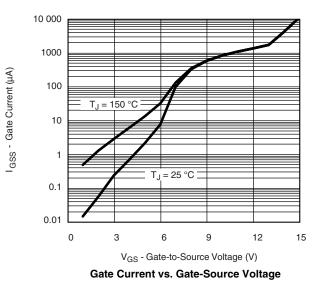
Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





10 _____

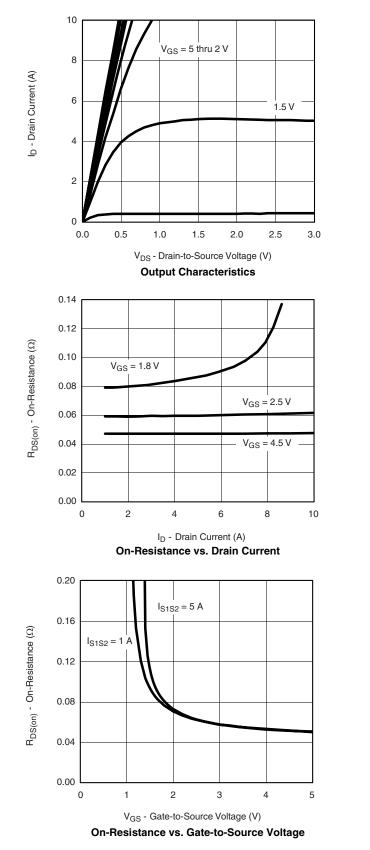
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

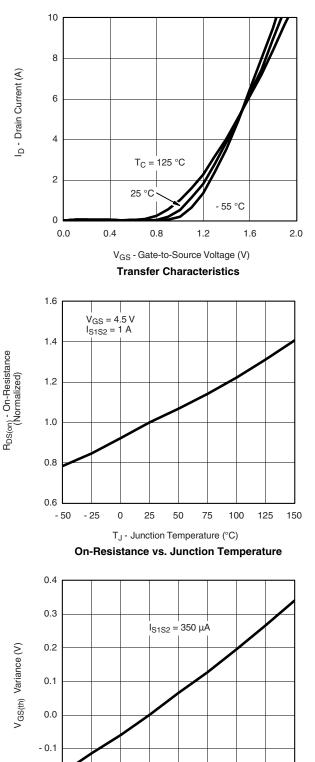


Si8901EDB

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





50

T_J - Temperature (°C)

Threshold Voltage

75

100

125

- 0.2

- 50

- 25

0

25

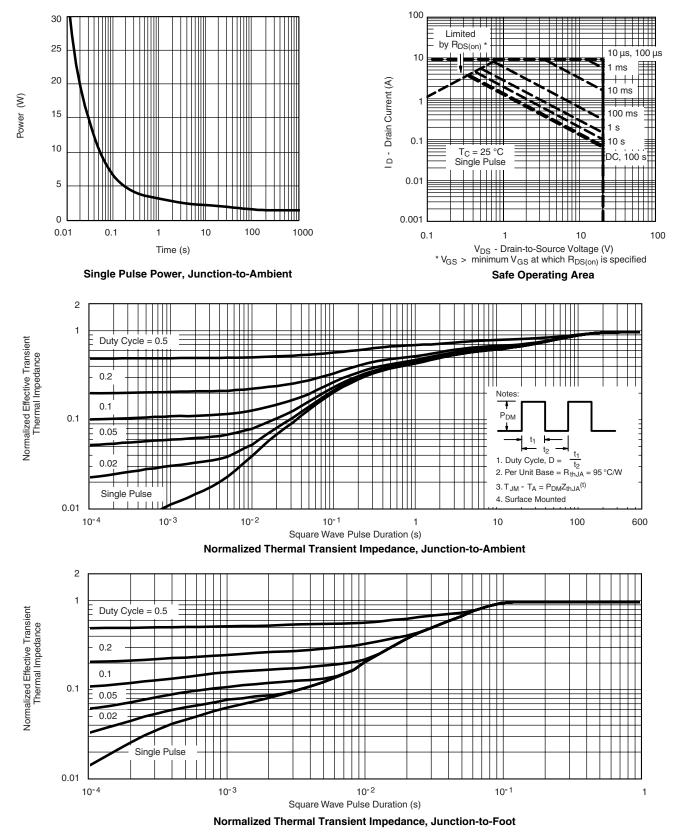
150

Si8901EDB





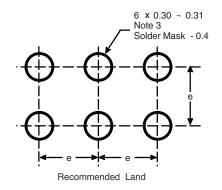
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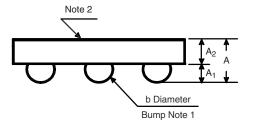


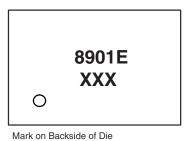


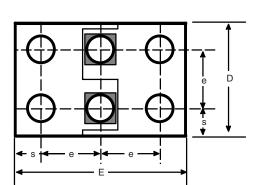
PACKAGE OUTLINE

MICRO FOOT: 6-BUMP (2 x 3, 0.8 mm PITCH)









Notes (Unless Otherwise Specified):

1. 6 solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.

2. Backside surface is coated with a Ag/Ni/Ti layer.

3. Non-solder mask defined copper landing pad.

4. Laser marks on the silicon die back.

Dim.	Millim	eters ^a	Inches		
	Min.	Max.	Min.	Max.	
Α	0.600	0.650	0.0236	0.0256	
A ₁	0.260	0.290	0.102	0.114	
A ₂	0.340	0.360	0.0134	0.0142	
b	0.370	0.410	0.0146	0.0161	
D	1.52	1.6	0.0598	0.0630	
E	2.32	2.4	0.0913	0.0945	
e	0.750	0.850	0.0295	0.0335	
S	0.380	0.400	0.0150	0.0157	

Notes:

a. Use millimeters as the primary measurement.

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